

Dual N-Channel Enhancement Mode Field Effect Transistor

Features

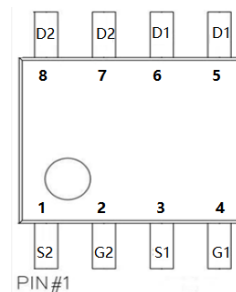
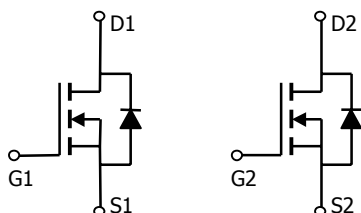
$V_{DS} (V) = 20V$

$I_D = 7A$

$R_{DS(ON)} < 26m\Omega (V_{GS} = 4.5V)$

$R_{DS(ON)} < 33m\Omega (V_{GS} = 2.5V)$

$R_{DS(ON)} < 42m\Omega (V_{GS} = 1.8V)$



SOP-8

Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	7
		$T_A=70^\circ C$	6
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	40	
Power Dissipation	$P_D$	$T_A=25^\circ C$	2
		$T_A=70^\circ C$	1.44
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10s$	48	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	74	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	35	40	$^\circ C/W$

**Dual N-Channel Enhancement Mode Field Effect Transistor**
**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	0.3	0.5	0.8	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	30			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A T <sub>J</sub> =125°C		21.6	26	mΩ
				29.2	36	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A		26.4	33	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =4A		33.3	42	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A		22		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A		0.76	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				3	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =10V, f=1MHz		1050		pF
C <sub>OSS</sub>	Output Capacitance			163		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			129		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		4		Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, I <sub>D</sub> =7A		15.2		nC
Q <sub>gs</sub>	Gate Source Charge			1		nC
Q <sub>gd</sub>	Gate Drain Charge			4		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =5V, V <sub>DS</sub> =10V, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		6.5		ns
t <sub>r</sub>	Turn-On Rise Time			9		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			56.5		ns
t <sub>f</sub>	Turn-Off Fall Time			13.2		ns
t <sub>rr</sub>	Body Diode Reverse Recovery time		I <sub>F</sub> =5A, di/dt=100A/μs		21	
Q <sub>rr</sub>	Body Diode Reverse Recovery charge	I <sub>F</sub> =5A, di/dt=100A/μs		7.1		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

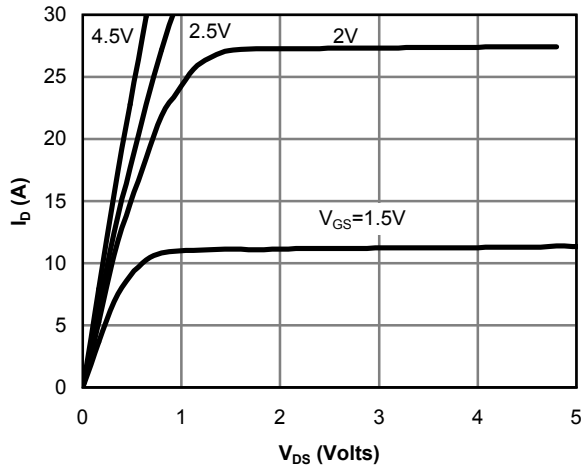


Fig 1: On-Region Characteristics

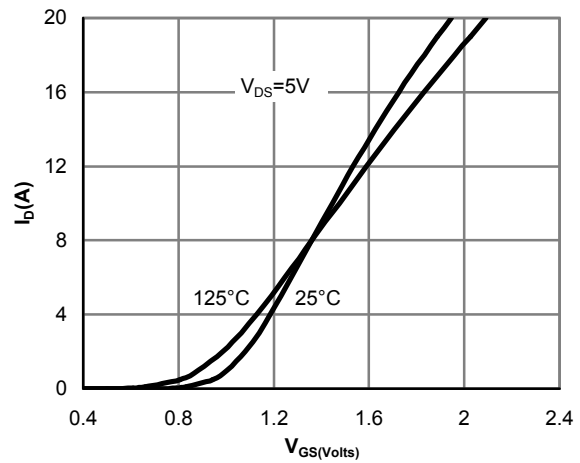


Figure 2: Transfer Characteristics

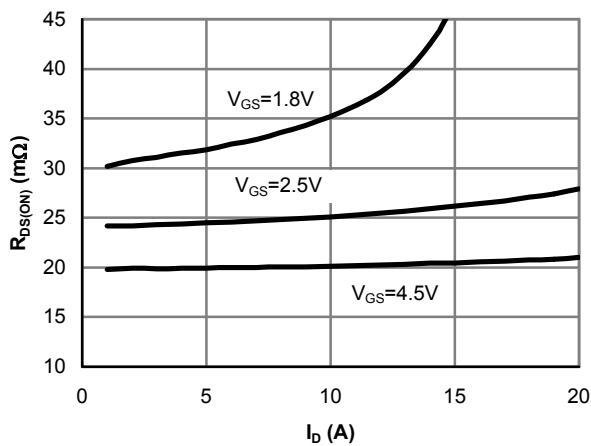


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

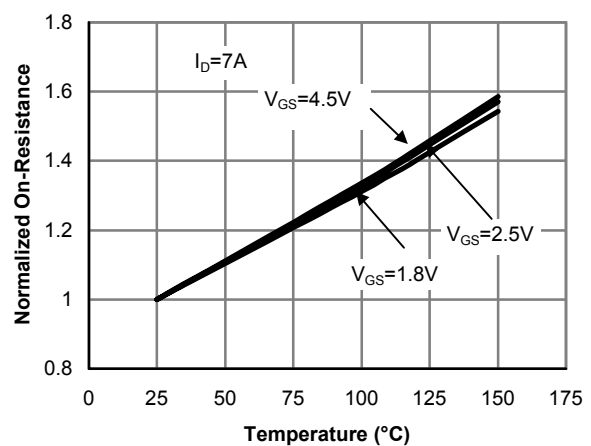


Figure 4: On-Resistance vs. Junction Temperature

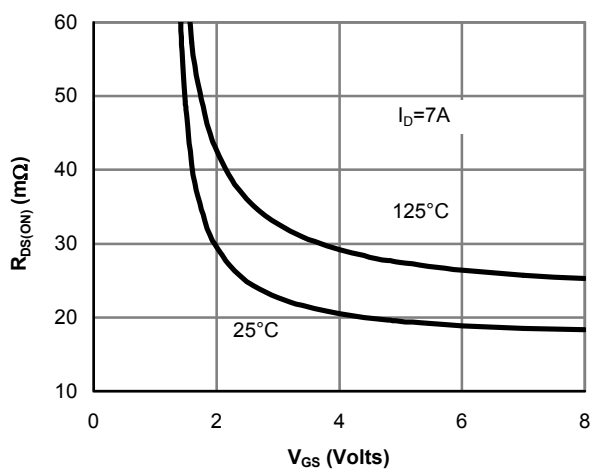


Figure 5: On-Resistance vs. Gate-Source Voltage

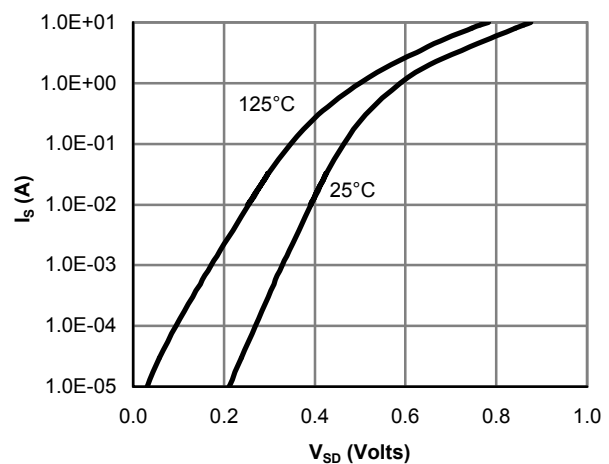


Figure 6: Body-Diode Characteristics

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

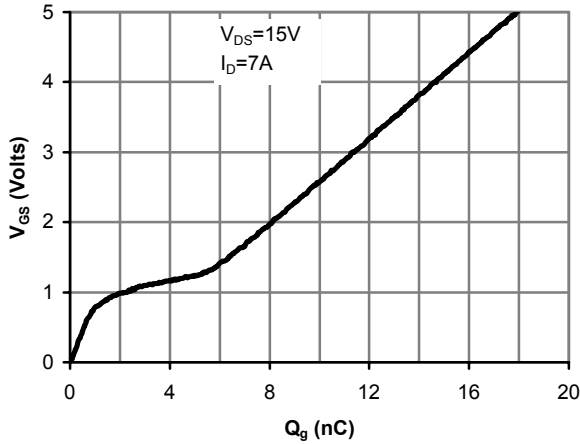


Figure 7: Gate-Charge Characteristics

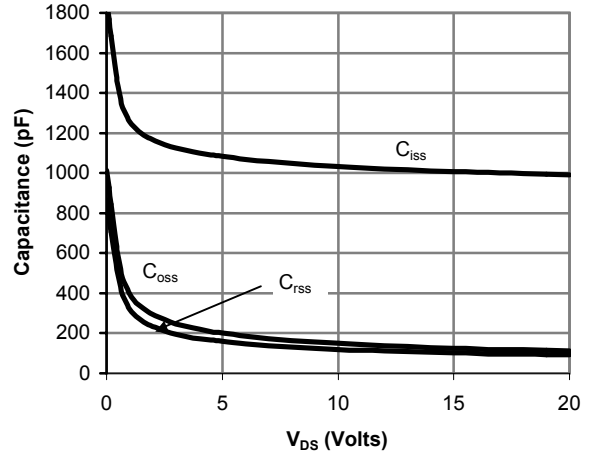


Figure 8: Capacitance Characteristics

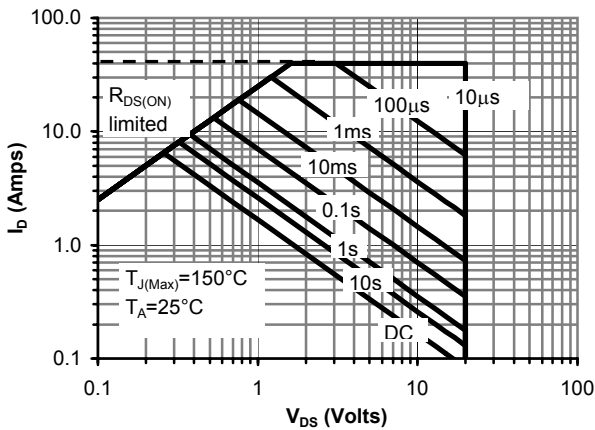


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

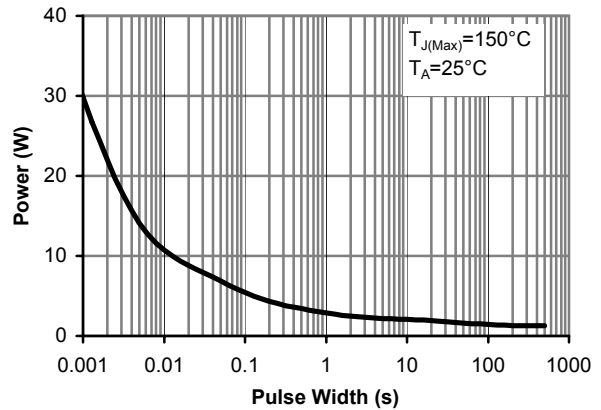


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

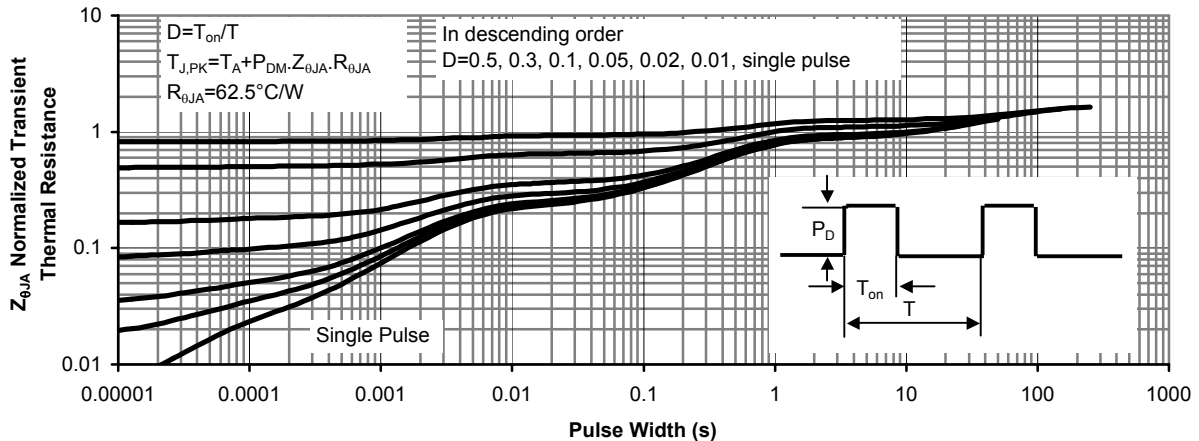
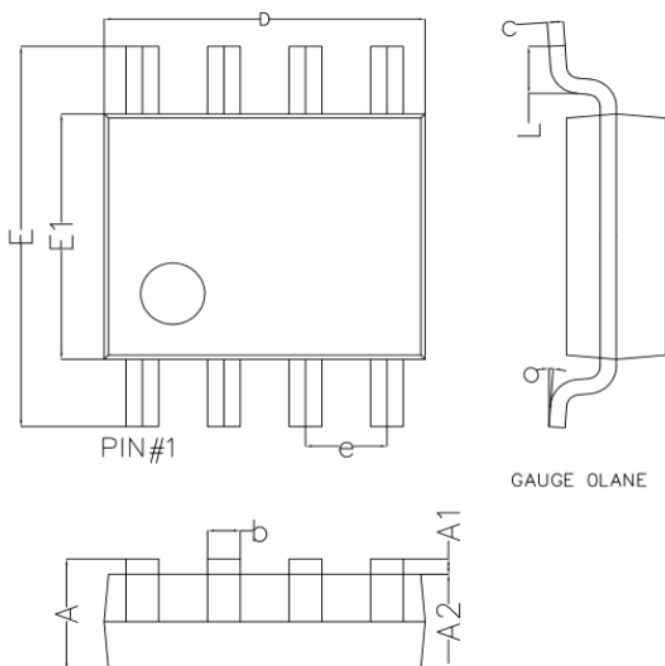


Figure 11: Normalized Maximum Transient Thermal Impedance

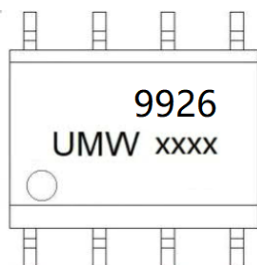
**Dual N-Channel Enhancement Mode Field Effect Transistor**

**Package Mechanical Data-SOP-8**



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270 (BSC)		
E	5.800	6.000	6.200
E1	3.800	3.900	4.000
L	0.400	0.835	1.2700
o	0°	4°	8°

**Marking**



("xxxx"代表年份周期)

**Ordering information**

Order Code	Package	Baseqty	Deliverymode
UMW CEM9926A	SOP-8	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)